

Atomic Layer Deposition at the Stanford Nanofabrication Facility

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NNIN ALD Workshop

ALD Equipment @ SNF all Cambridge Nanotech

Equipment	Online	Cleanliness	Comments
savannah	Fall 2009	MOS until summer 2012 now open	Metal oxides only currently. Previously a lot of metal nitride work
fiji1	Summer 2011	MOS clean	One half of a F202 system; metal oxides, metal nitrides, and BEOL MOS metals
fiji2	Summer 2012	Open to “all materials”	Heavy utilization (80% or more of 24/7); metal oxides, metal nitrides, metals
fiji3	Winter 2013	Open to “all materials”	Oxide only processing; also to meet capacity demand of fiji2
Savannah-mvd	Winter/Spring 2013	Open to “all materials”	<ul style="list-style-type: none"> - Incorporated into a glovebox - Plasma cleaner also in glovebox - Molecular Vapor Deposition

Films available @ SNF – Extensive Characterization

- **Al₂O₃**
 - Thermal (TMA + H₂O)
 - Plasma (TMA + O₂ plasma)
- **HfO₂**
 - Thermal (TDMA-Hf + H₂O)
 - Plasma (TDMA-Hf + O₂ plasma)
- **TiO₂**
 - Thermal (TDMA-Ti + H₂O)
 - Plasma (TDMA-Ti + O₂ plasma)
- **ZrO₂**
 - Thermal (TDMA-Zr + H₂O)
 - Plasma (TDMA-Zr + O₂ plasma)
- **SiO₂** (Plasma 3DMAS + O₂ plasma)
- **Pt**
 - Thermal (Me(CpMe)Pt + O₂)
 - Plasma (Me(CpMe)Pt + O₂ plasma (+ H₂ plasma))
- **TiN**
 - Thermal (TDMA-Ti + NH₃)
 - Plasma (TDMA-Ti + N₂ plasma)
 - Plasma (TDMA-Ti + NH₃ plasma – *early stages*)
- **ZnO**
 - Thermal (DEZ + H₂O)
- **Ta₂O₅**
 - Thermal (TDEMATB-Ta + H₂O)
 - Plasma (TDEMATB-Ta + O₂ plasma)

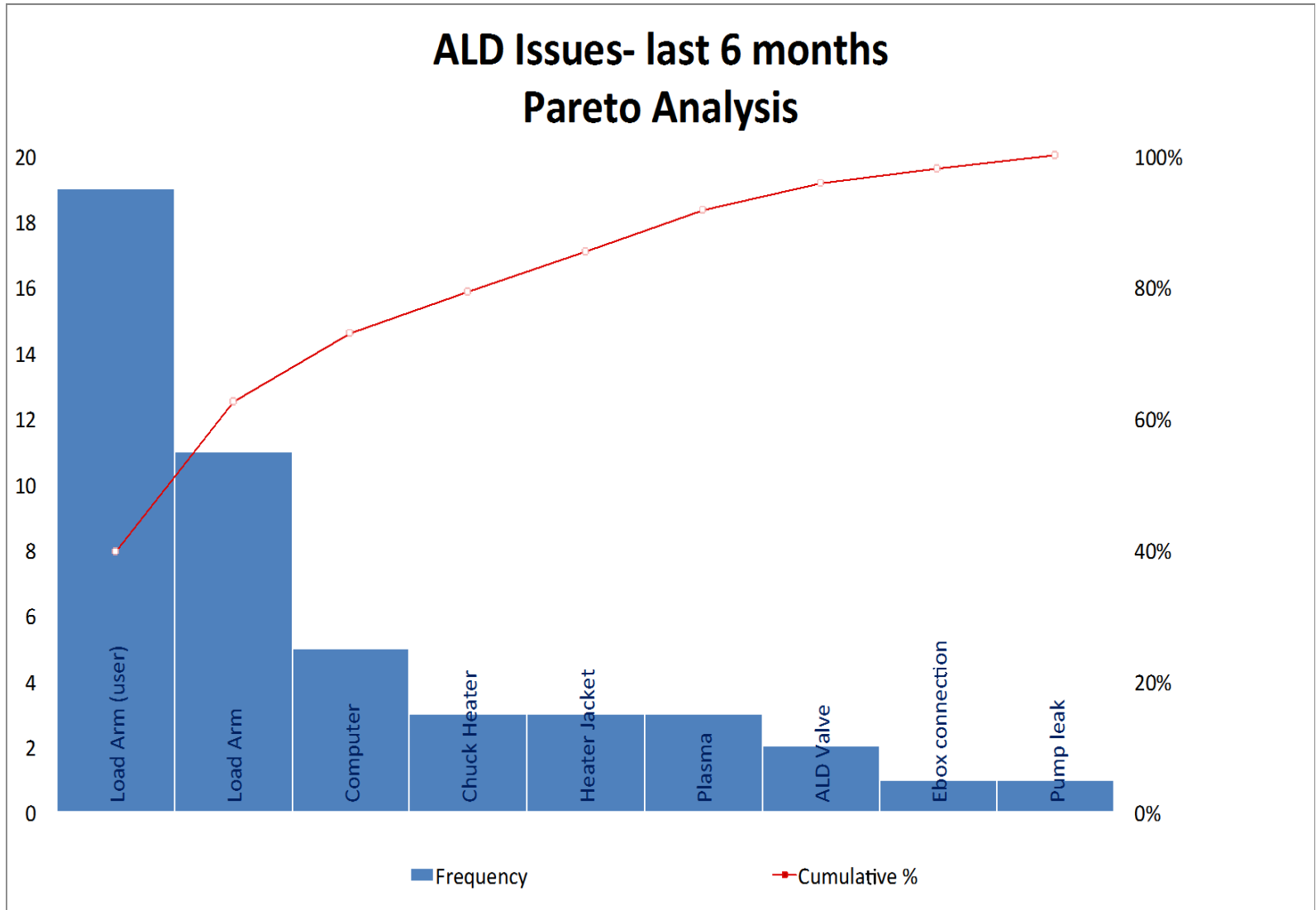
Films available @ SNF – Demonstrated Deposition

- **HfN (Hf₃N₄ really)**
 - Thermal (TDMA-Hf + NH₃)
 - Plasma (TDMA-Hf + N₂ plasma)
- **WO_x**
 - Thermal (BTDBMA-W + H₂O)
 - Plasma (BTDBMA-W + O₂ plasma)
- **WN**
 - Thermal (BTDBMA-W + NH₃)
 - Plasma (BTDBMA-W + N₂ plasma)
- **Ru**
 - Thermal ((CpEt)Ru + O₂)
- **SnO**
 - Thermal (TDMA-Sn + H₂O₂)
- **InO**
 - Thermal (CpIn + H₂O)
- **ITO** (see above)
- **Y₂O₃ (!)**
 - Thermal (Me(3MeCp)Y + H₂O or Me(2MeEtCp)Y + H₂O)
- **YSZ (yttria + zirconia)**
- **AZO (see above)**
- **NiO_x**
 - Thermal (nickelocene + H₂O)
 - Ni from H₂ plasma reduction
- **FeO_x**
 - Thermal (ferrocene + H₂O)
 - Fe from H₂ plasma reduction
- **AlN**
 - Plasma (TMA + N₂ plasma)
- **SrO**
 - Thermal (MeCpSr + H₂O)
- **SiO₂**
 - Thermal (tert-butoxy silanol + TMA)
 - YIKES!!! – discontinued.

Films @ SNF – Wish List

- TaN
- Ti
- Plasma Ru (better nucleation)
- W
- Y_2O_3
- Ideally want to support anything requested

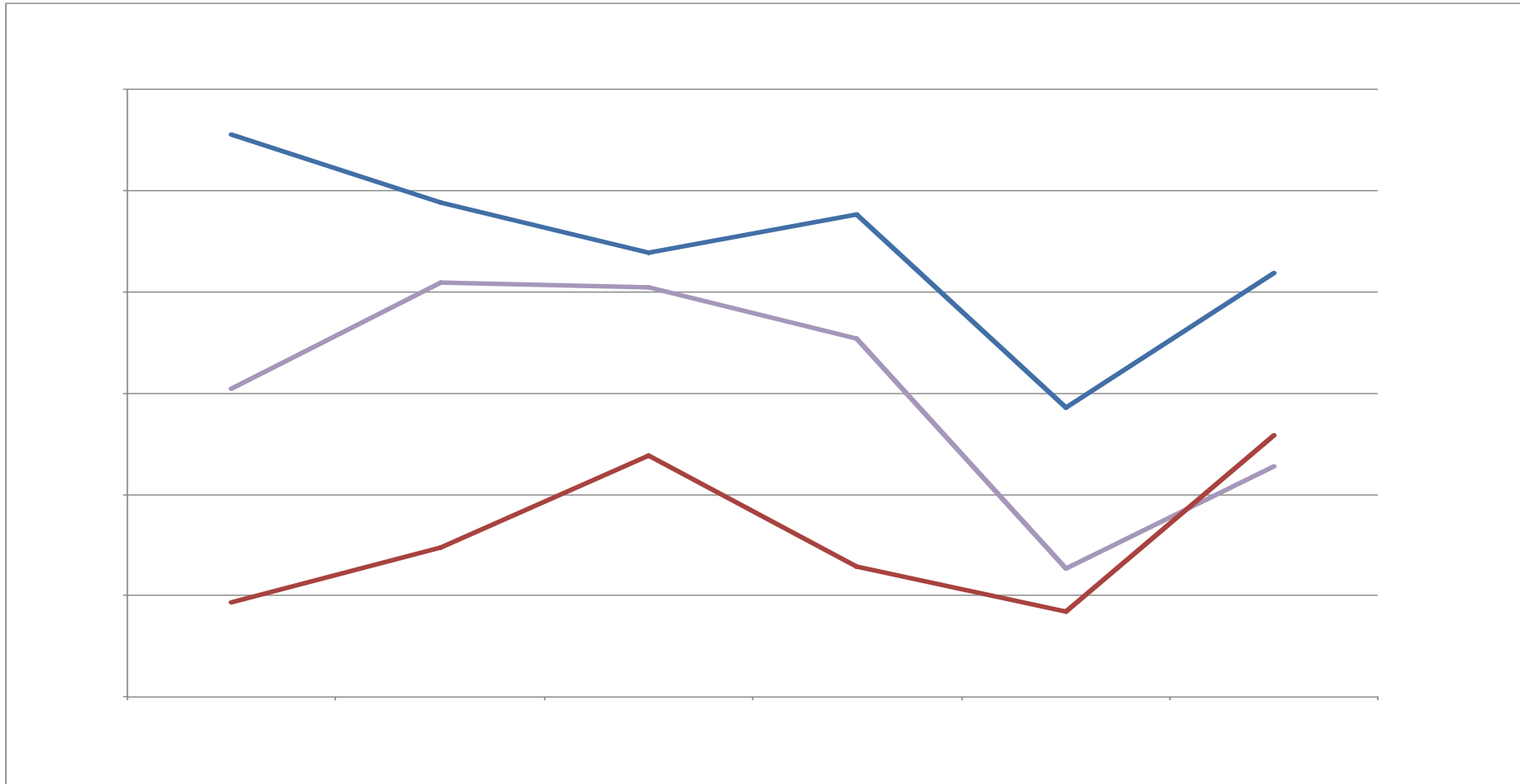
ALD Issues Pareto (last 6 months)



Primary Issues

- Primary issues related to Fiji load arms.
 - Most issues related to user error.
 - Fiji2 loading arm required refurbishment after being bent by user.
 - After summer break there was a large spike in errors. Once users re-familiarized themselves with loading process, error frequency dropped.
 - Setting screws to secure loading arm height also tend to drift and re-calibration of arm height is second most common error.
 - Fortunately these errors are relatively easy to recover from and result in minimal equipment downtime.

Tool Usage



fiji2

fiji1

savannah

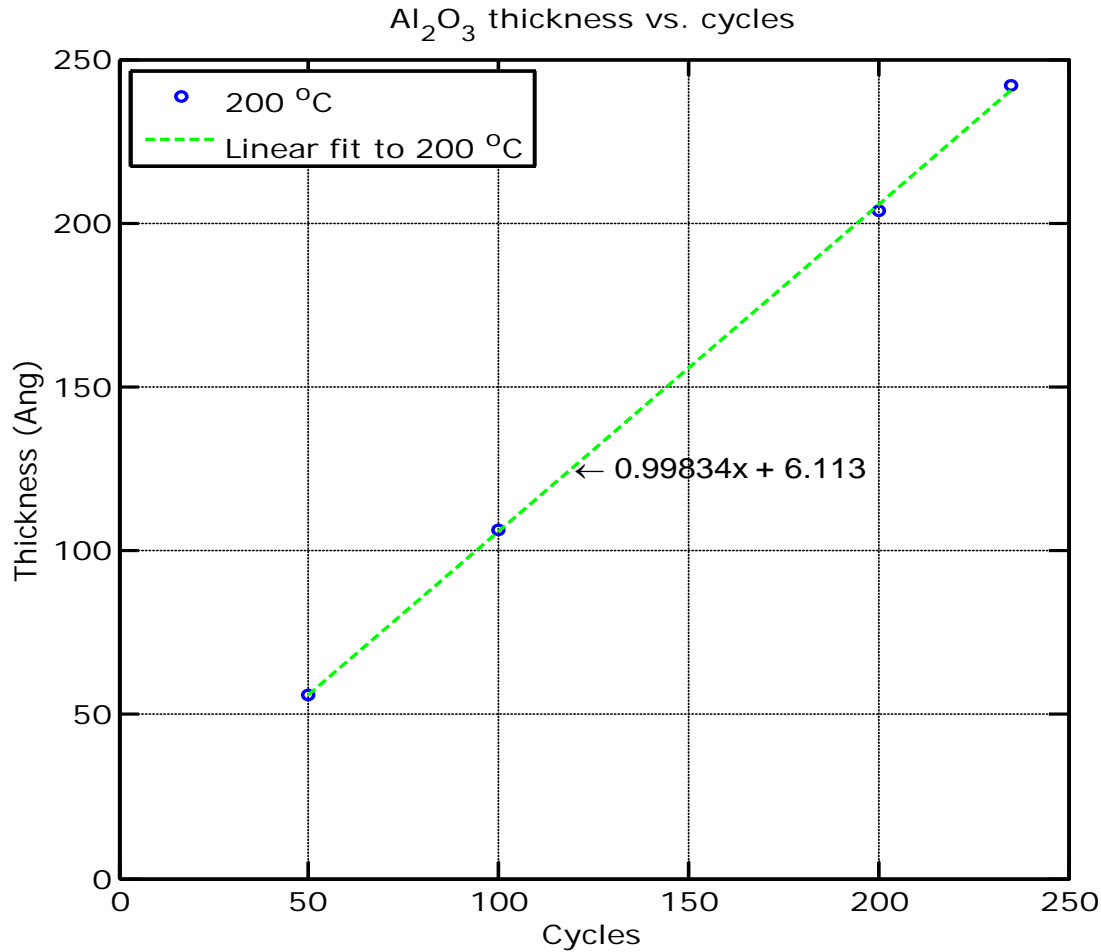
Maintenance Schedule

- Savannah
 - Reset pressure gauge (2x/yr)
 - Pump rebuild (1/yr); change oil (2x/yr)
 - Kalrez O-Ring (1/yr)
 - Chamber CO₂ clean: 1/yr (during shutdown)
 - Manifold clean: 4μm of film (coming soon)
- Fiji
 - Sample holder clean: As needed (~2X/year)
 - Load Arm refurbishment: Recommended 1/year
 - Chamber clean: haven't done yet
 - Manifold clean: 4μm of film

Additions to system

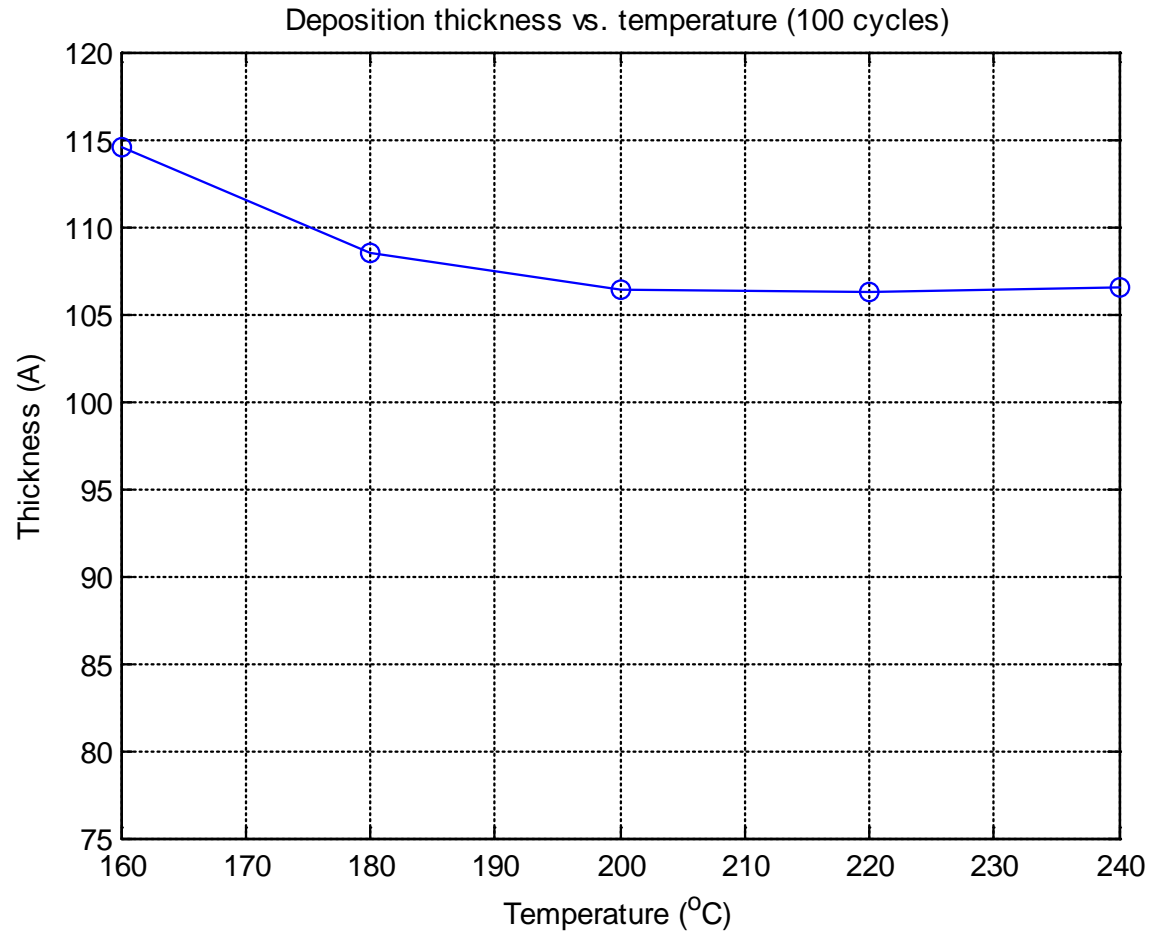
- We added a boost system in fall 2012 to aid with low volatility precursors
 - Similar to a bubbler
 - Very positive results (SrO and Y_2O_3)
 - Desire to add to more chambers
- Wish list
 - In situ film measurement
 - QCM
 - Ellipsometry (not really possible in several of our systems)
 - Ozone

Material Characterization: Al_2O_3



- Found deposition rate @ 200 °C: ~ 0.99 A/cycle

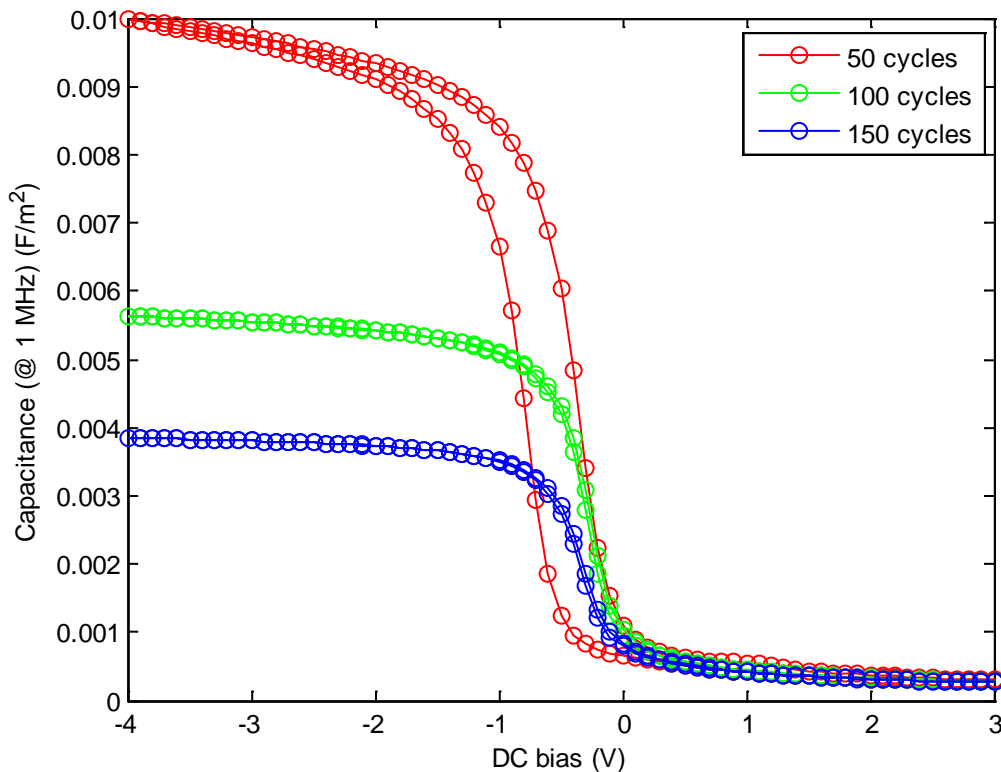
Material Characterization: Al_2O_3



- Deposition rate decreases with temperature increase

Material Characterization: Al_2O_3

- Dielectric constant is extracted from accumulation capacitance & measured dielectric thickness

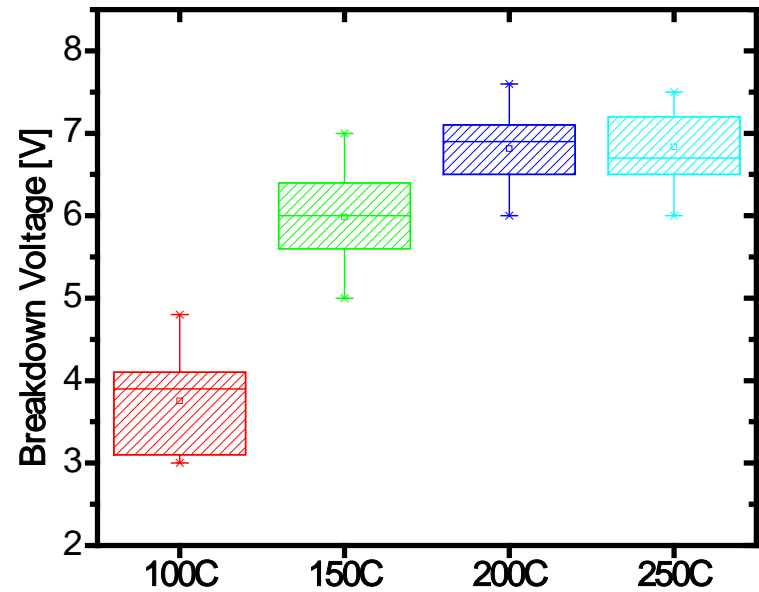
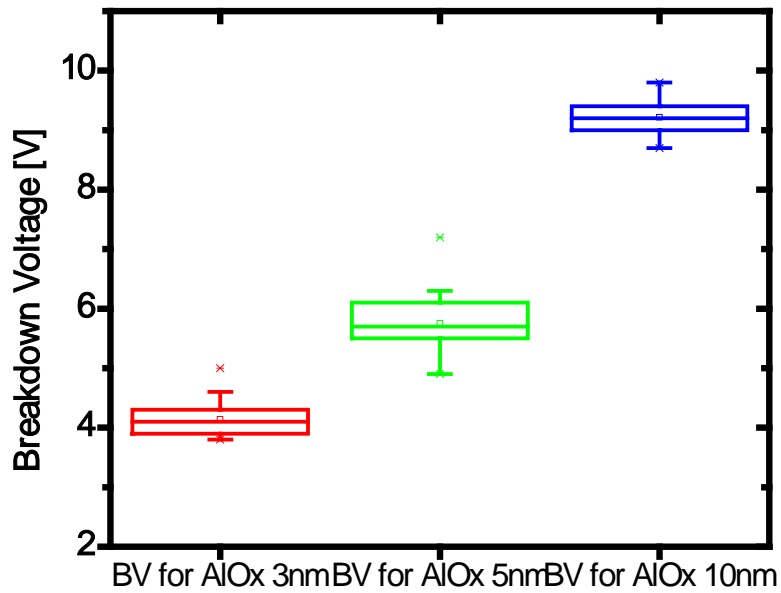


Cycles	Dielectric Constant (k)
50	6.30
100	6.77
150	6.74
200	6.76

·Deposition temperature: 200 °C

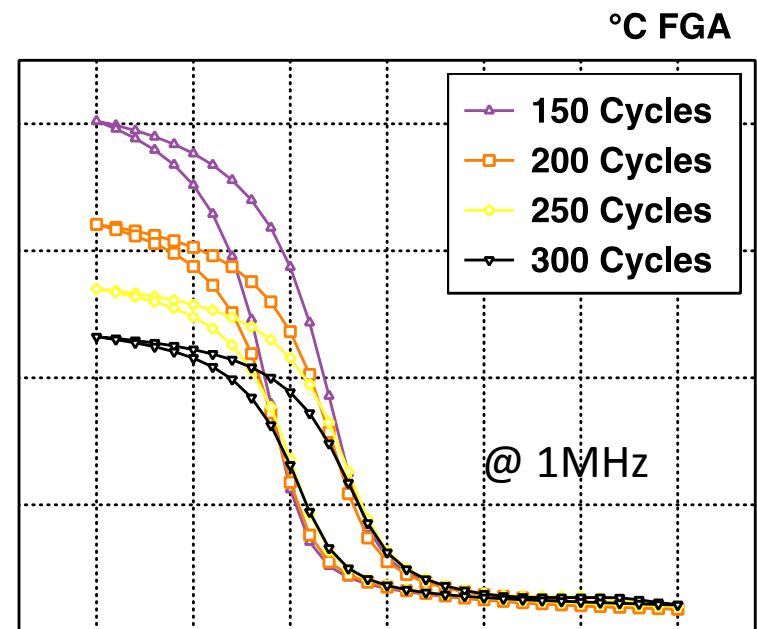
Extracted dielectric constant: ~6.75

Material Characterization: Al₂O₃



Other well characterized metal oxides

- Similar data is available at the tool's website
 - Example HfO_2



Average Dielectric Constant : 15.27

Average Doping Concentration: $1.5 \times 10^{16} / \text{cm}^3$

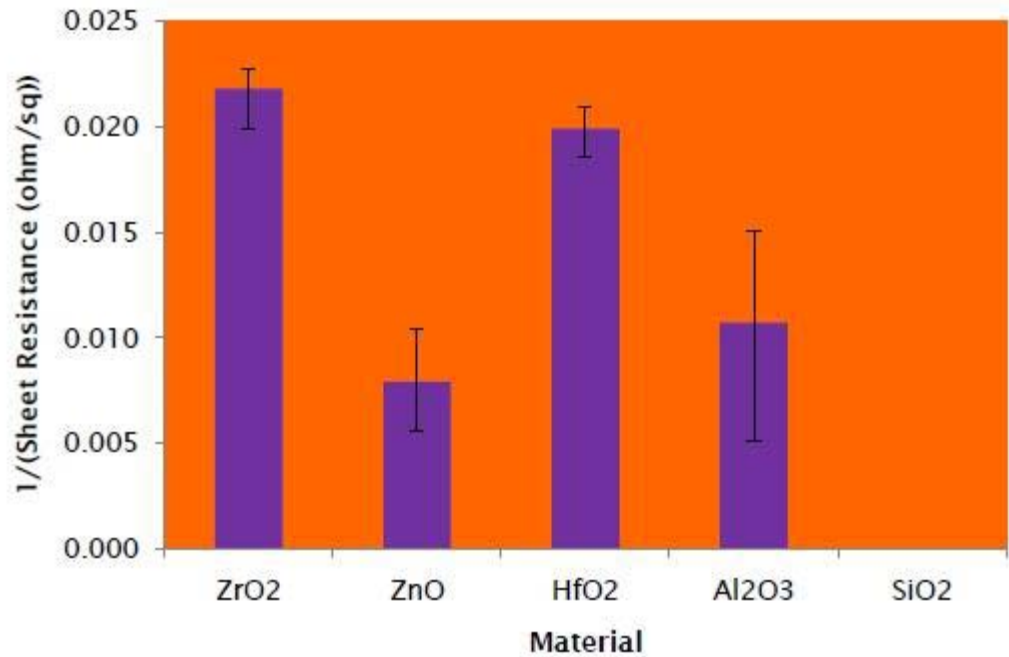
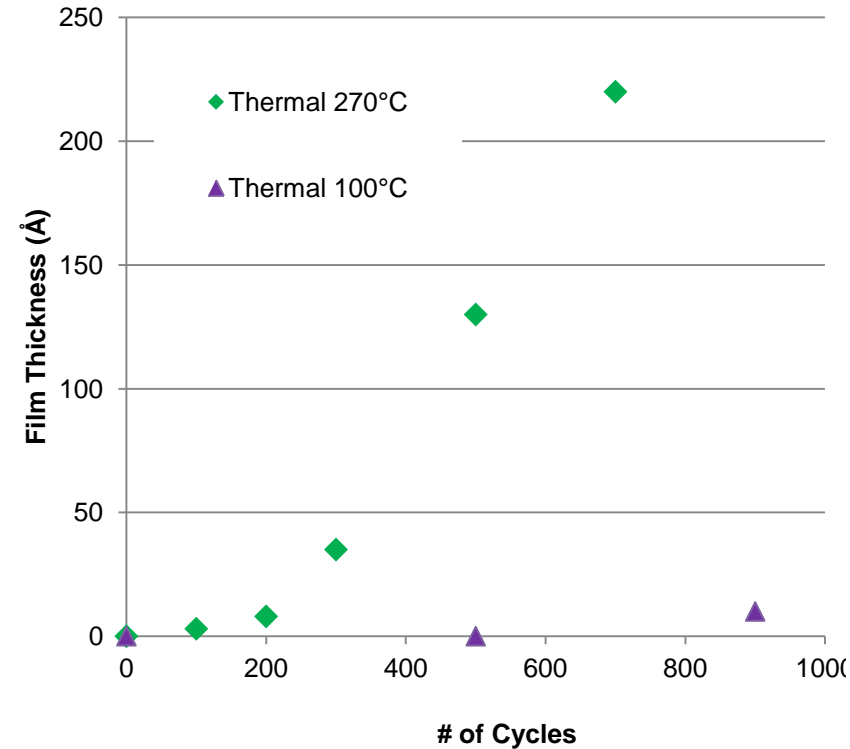
Hysteresis Range: 230mV-285mV

Mobile Charge Range: $8 \times 10^{11} / 1.4 \times 10^{12} / \text{cm}^2$

- Dielectric Constant (k), doping type and concentration were extracted at 1MHz.

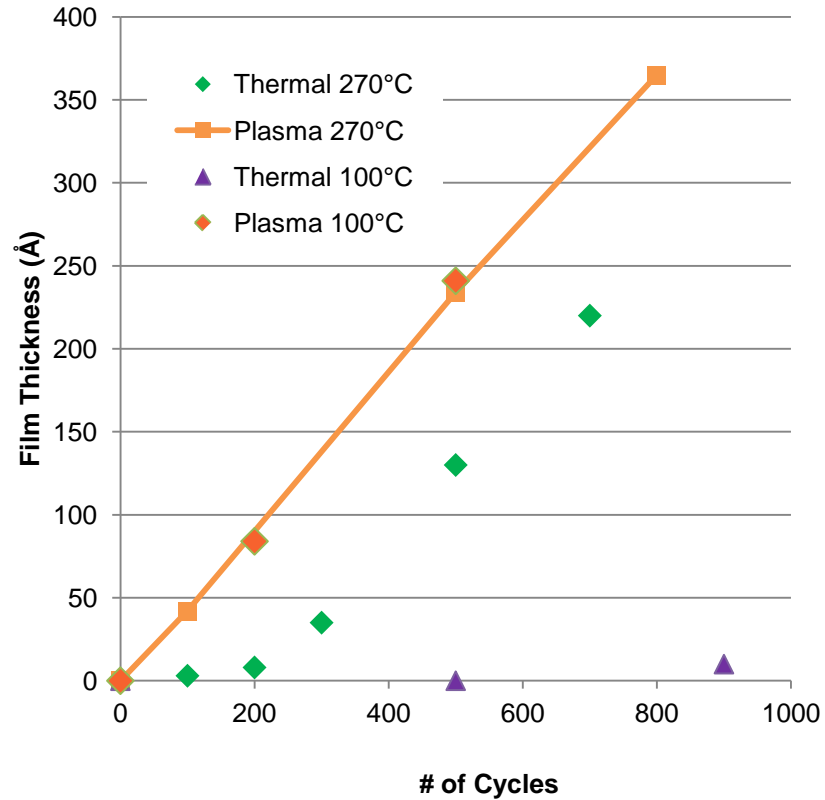
Pt and Nucleation

Thermal Pt from MeCpPtMe₃ and O₂



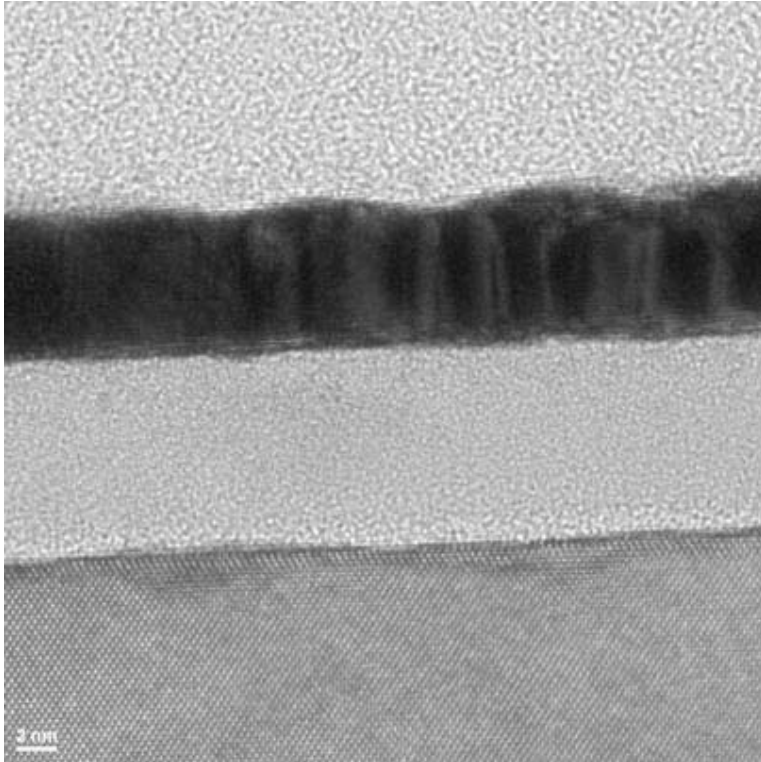
Pt and Nucleation

Plasma Pt from MeCpPtMe₃ and O₂

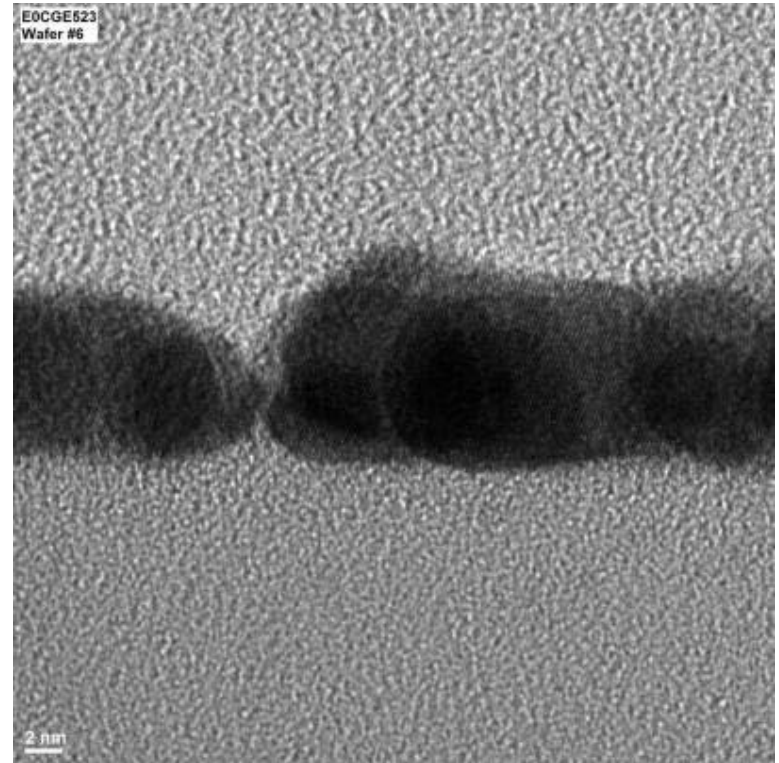


Pt and Nucleation

Plasma Pt from MeCpPtMe_3 and O_2



Plasma ALD Pt on Al_2O_3



Plasma ALD Pt on thermal SiO_2

TiN: Thermal vs Plasma

- Oxygen content kills conductivity of TiN
- With savannah we never saw less than 15% atomic weight in oxygen ($\text{m}\Omega\text{-cm}$ level resistivity)
- Switching to plasma in fiji 1% oxygen and best result is $10\mu\Omega\text{-cm}$ resistivity
- How well can the load locked, higher temp fiji do for thermal TiN?

Open questions of interest

- How to handle ZnO?
- General contamination concerns...
 - Sulfide ALD for instance
- Utilizing the tool for non-ALD projects
- Coating of powders and loose material
- Training and theory background for users
- Anyone with a fiji: load transfer arms

Thank you.
Any questions?

